

APPLICATION NOTE 2908

Hot-Swap Controller IC Makes Adjustable Circuit Breaker

Abstract: Use of a hot-swap controller IC provides inrush-current-limiting and circuit-breaker functions for medium to high-voltage circuit protection.

Medium- and high-voltage systems that range from 9V to 72V often require one or more of the following circuit capabilities: hot-swap control, circuit-breaker fault protection, and inrush current limiting.

The circuit of **Figure 1** provides inrush current limiting and a reliable circuit-breaker function for the load (C1 and R2), yet contains only a p-channel MOSFET, a hot-swap controller IC, and two optional resistors (R1 and R3). Adding a low-value resistor at the MOSFET drain provides an adjustable trip-point and improved accuracy over the operating temperature range (**Figure 2**).

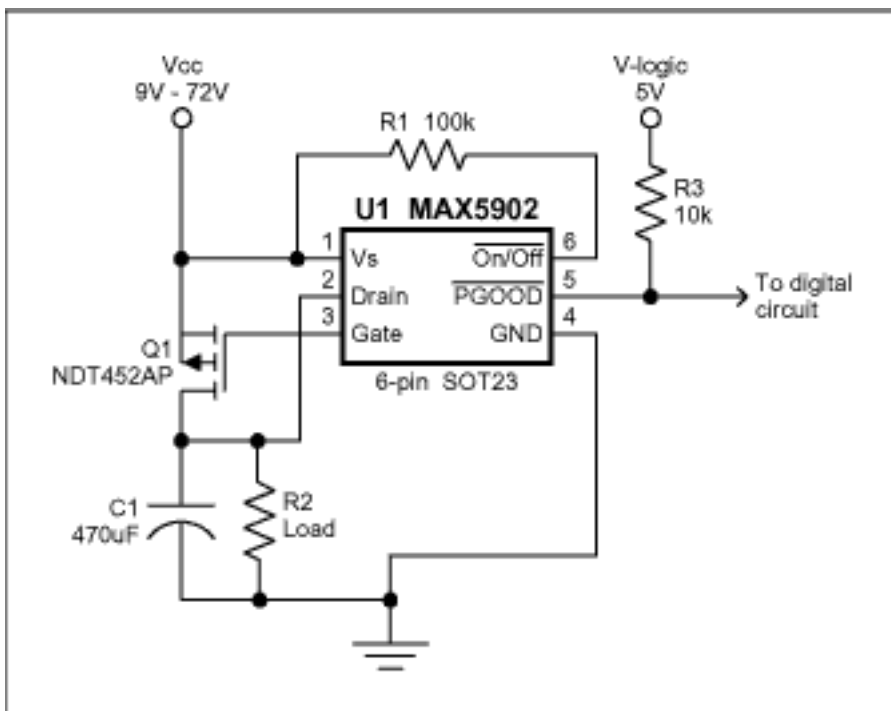


Figure 1. Standard circuit-breaker application.

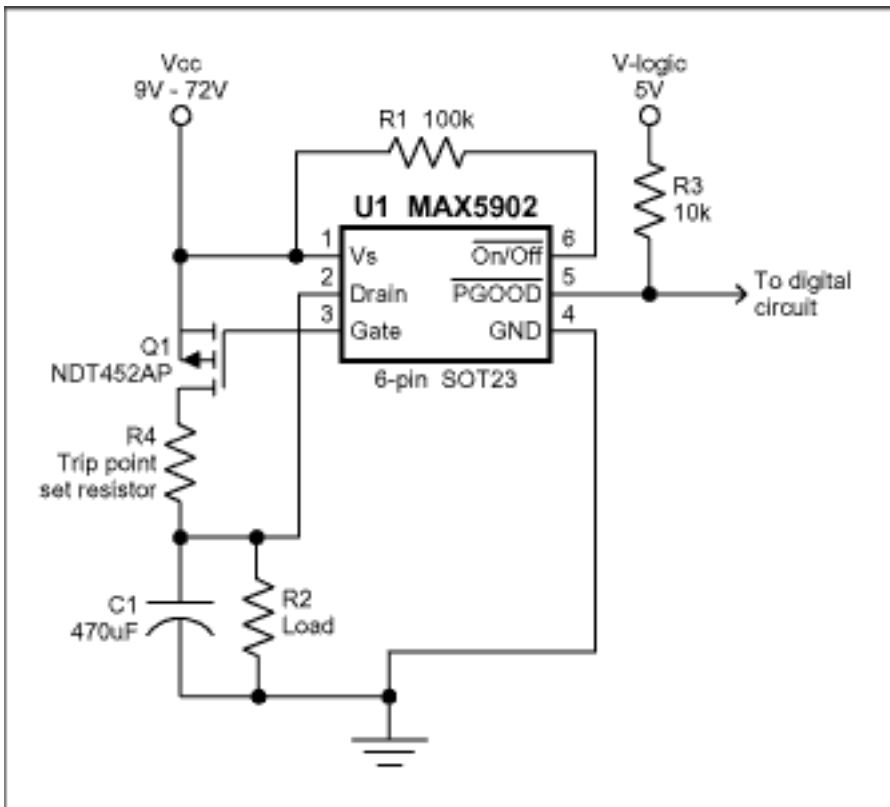


Figure 2. Adding a trip-point-adjust resistor (R4) to the circuit of Figure 1 improves its initial accuracy and accuracy over temperature.

For hot-swap applications, U1 limits the inrush current based on a typical gate-drive slew rate of 9V/mS. Inrush current is given by the equation $I = CdV/dT = CSR$, where C = load capacitance and SR is the slew rate, set by U1 at 9V/mS (typical). For a load capacitance of 100 μ F, the IC limits inrush current to approximately 0.9A.

U1's circuit-breaker function uses an internal comparator and the MOSFET on-resistance ($R_{DS(ON)}$) to sense a fault condition. ($R_{DS(ON)}$) for Q1 is typically 52m Ω and U1 has selectable circuit-breaker trip points (CB) of 300mV, 400mV, or 500mV. At the lowest trip point (300mV), the CB trip current at $T_J = 25^\circ\text{C}$ is typically 5.77A.

The circuit breaker's voltage-trip value is determined from the equation $V_{CB} > (R_{DS(ON)})I_{LOAD(MAX)}$, or $V_{CB}/I_{LOAD(MAX)} > (R_{DS(ON)})$.

Suppose the desired limit is 2A. Using typical values,

$$300\text{mV}/2\text{A} \approx 150\text{m}\Omega > (R_{DS(ON)})$$

Instead of substituting another MOSFET with higher on-resistance, add a $\approx 100\text{m}\Omega$ resistor in series with Q1 (i.e., R4 in Figure 2). Besides allowing adjustable circuit-breaker levels, R4 provides better circuit-breaker accuracy and improved stability over temperature. For example, ($R_{DS(ON)}$) for Q1 is $\approx 52\text{m}\Omega$ @ $T_J = 25^\circ\text{C}$ and $\approx 130\text{m}\Omega$ @ $T_J = 125^\circ\text{C}$, a change of 150%. If you add a 100m Ω , 100ppm/ $^\circ\text{C}$ resistor (which varies by 0.001 Ω from 25 $^\circ\text{C}$ to 125 $^\circ\text{C}$), the combined variance from 25 $^\circ\text{C}$ (152m Ω) to 125 $^\circ\text{C}$ (231m Ω) is only 79m Ω , which is 52%.

This former Design Brief was published in the November 10, 2003 issue of *ED* magazine.

Application Note 2908: <http://www.maxim-ic.com/an2908>

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